Plastic Point Source Infrared Emitting Diode

OP245PS



Features:

- Point source irradiance pattern
- Side-looking package for space-limited applications
- Wavelength matched to silicon's peak response
- Higher power output than GaAs at equivalent drive currents
- Fast switching speed



Description:

Each OP245PS device is an infrared emitting diode with a 850 nm GaAIAs chip, molded in a clear IR-transmissive sidelooking epoxy package. This package makes these devices ideal for PC Board mounted slotted switches and for mounted interrupt detectors.

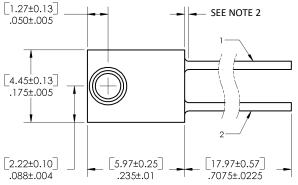
The stable forward V_F vs T_A characteristic make them suitable for applications that have limited voltage, such as battery operation; whereas, the low T_R/T_F makes them ideal for high-speed operations.

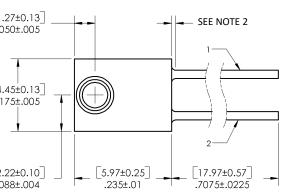
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

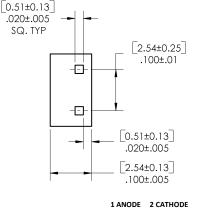
Applications:

- Space-limited applications
- PC Board mounted slotted switch
- Mounted interrupt detector
- · High-speed applications

Ordering Information								
Part Number	LED Peak Wavelength	Lens Type	Total Beam Angle	Lead Length (min.)				
OP245PS	850 nm	Recessed Dome	±18°	0.5" / 12.7 mm				







Pin# **LED** Anode

Cathode

[MILLIMETERS] DIMENSIONS ARE IN: INCHES

NOTES:

- 1. OUTSIDE DISCRETE SHELL IS POLYSULFONE.
- 2. MAX ALLOWABLE EPOXY MENSCUS IS 0.010".



CONTAINS POLYSULFONE

To avoid stress cracking, we suggest using ND Industries' Vibra-Tite for thread-locking Vibra-Tite evaporates fast without causing structural failure in OPTEK'S molded plastics

General Note

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current	1.0 A
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron] (1)	260° C
Power Dissipation (2)	100 mW

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS			
Input Diod	nput Diode								
E _{E (APT)} (3)	Apertured Radiant Incidence	0.12	-	0.8	mW/cm ²	I _F = 20 mA			
V _F	Forward Voltage	1.2	-	1.7	V	I _F = 20 mA			
I _R	Reverse Current	-	10	-	μΑ	V _R = 2 V			
λ_{P}	Wavelength at Peak Emission	-	850	-	nm	I _F = 20 mA			
В	Spectral Bandwidth between Half Power Points	-	50	-	nm	I _F = 20 mA			
θ_{HP}	Emission Angle at Half Power Points	-	±18°	-	Degree	I _F = 20 mA			
t _r	Output Rise Time	-	10	-	ns	$I_{F(PK)}$ = 20 mA, PW = 10 μ s, D.C. = 10%			
t _f	Output Fall Time	-	10	-	ns	$I_{F(PK)}$ = 20 mA, PW = 10 μ s, D.C. = 10%			

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly 1.07 mW/° C above 25° C.
- 3. E_{E(APT)} is a measurement of the average apertured radiant energy incident upon a sensing area 0.180" (4.57 mm) in diameter perpendicular to and centered on the mechanical axis of the lens and 0.653" (16.6 mm) from the lens tip. E_{E(APT)} is not necessarily uniform within the measured area.

Rev C 07/2025 Page 2

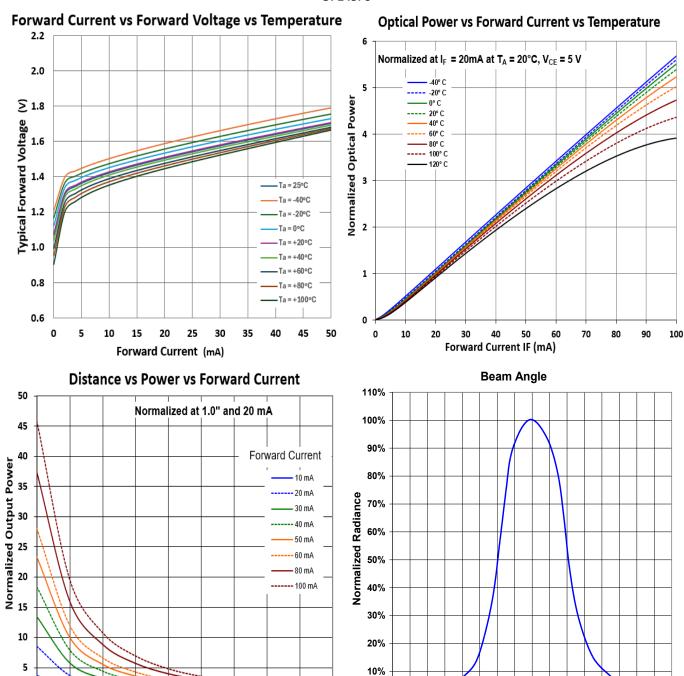
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OP245PS



Typical Performance

OP245PS



General Note

0.2

TT Electronics reserves the right to make changes in product specification without notice or liability. All information is subject to TT Electronics' own data and is considered accurate at time of going to print.

Distance (inches)

0.8

-80 -70 -60 -50 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 Degrees

0.4